Smart Two Channel Highside Power Switch

Features

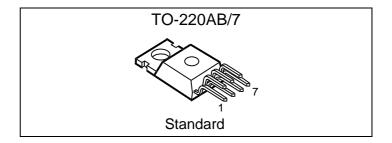
- Overload protection
- Current limitation
- Short circuit protection
- Thermal shutdown
- Overvoltage protection (including load dump)
- Reverse battery protection¹⁾
- Undervoltage and overvoltage shutdown with auto-restart and hysteresis
- Open drain diagnostic output
- Open load detection in ON-state
- CMOS compatible input
- Loss of ground and loss of V_{bb} protection
- Electrostatic discharge (ESD) protection

Application

- μC compatible power switch with diagnostic feedback for 12 V DC grounded loads
- Most suitable for resistive and lamp loads

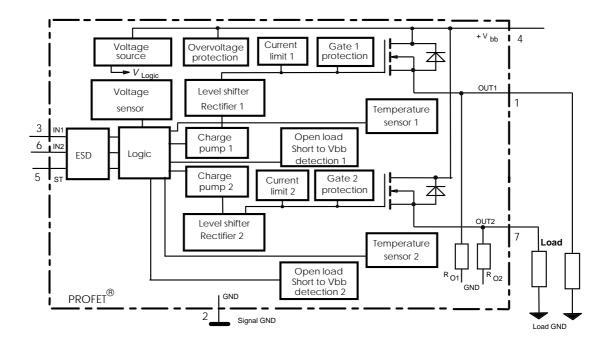
Product Summary

Overvoltage protection		b(AZ)	43	V
Operating voltage	b(on)	5.0 2	4 V	
oh	aaah	both		
CH	annels:	each	parallel	
On-state resistance	R_{ON}	200	100	$m\Omega$
Load current (ISO)	$I_{L(ISO)}$	2.3	4.4	Α
Current limitation	I _{L(SCr)}	5	5	Α



General Description

N channel vertical power FET with charge pump, ground referenced CMOS compatible input and diagnostic feedback, monolithically integrated in Smart SIPMOS® technology. Fully protected by embedded protection functions.



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With external current limit (e.g. resistor R_{GND} =150 Ω) in GND connection, resistor in series with ST connection, reverse load current limited by connected load.



Pin	Symbol	Function
1	OUT1 (Load, L)	Output 1, protected high-side power output of channel 1
2	GND	Logic ground
3	IN1	Input 1, activates channel 1 in case of logical high signal
4	Vbb	Positive power supply voltage, the tab is shorted to this pin
5	ST	Diagnostic feedback: open drain, low on failure
6	IN2	Input 2, activates channel 2 in case of logical high signal
7	OUT2 (Load, L)	Output 2, protected high-side power output of channel 2

Maximum Ratings at $T_j = 25$ °C unless otherwise specified

Parameter	Symbol	Values	Unit
Supply voltage (overvoltage protection see page 3)	$V_{ m bb}$	43	V
Supply voltage for full short circuit protection $T_{\rm jStart}$ =-40+150°C	$V_{ m bb}$	24	V
Load dump protection ²⁾ $V_{\text{LoadDump}} = U_{\text{A}} + V_{\text{S}}, U_{\text{A}} = 13.5 \text{ V}$ $R_{\text{I}}^{3)} = 2 \Omega, R_{\text{L}} = 5.3 \Omega, t_{\text{d}} = 200 \text{ ms}, \text{IN} = \text{low or high}$	V _{Load dump} ⁴⁾	60	V
Load current (Short circuit current, see page 4)	/ ∟	self-limited	Α
Operating temperature range	T _j	-40+150	°C
Storage temperature range	$T_{ m stg}$	-55+150	
Power dissipation (DC), T _C ≤ 25 °C	P _{tot}	36	W
Electrostatic discharge capability (ESD) IN: (Human Body Model) all other pins: acc. MIL-STD883D, method 3015.7 and ESD assn. std. S5.1-1993	V _{ESD}	1.0 2.0	kV
Input voltage (DC)	V_{IN}	-10 +16	V
Current through input pin (DC)	I _{IN}	±2.0	mΑ
Current through status pin (DC)	I _{ST}	±5.0	
see internal circuit diagrams page 6			

Thermal Characteristics

Parameter and Conditions		Symbol	Values			Unit
			min	typ	max	
Thermal resistance	chip - case, both channels: each channel:	R_{thJC}			3.5 7.0	K/W
	junction - ambient (free air):	R_{thJA}			75	

Supply voltages higher than $V_{bb(AZ)}$ require an external current limit for the GND and status pins, e.g. with a 150 Ω resistor in the GND connection and a 15 k Ω resistor in series with the status pin. A resistor for the protection of the input is integrated.

 $R_{\rm I}$ = internal resistance of the load dump test pulse generator

⁴⁾ V_{Load dump} is setup without the DUT connected to the generator per ISO 7637-1 and DIN 40839



Electrical Characteristics

Parameter and Conditions, each channel	Symbol		Values	;	Unit
at $T_j = 25$ °C, $V_{bb} = 12$ V unless otherwise specified		min	typ	max	

Load Switching Capabilities and Characteristics

On-state resistance (pin 4 t	to 1 or 7)					
<i>I</i> ∟ = 1.8 A	<i>T</i> _j =25 °C:	R_{ON}		160	200	$m\Omega$
each channel	<i>T</i> _j =150 °C:			320	400	
Nominal load current, ISO $V_{ON} = 0.5 \text{ V}$, $T_C = 85 \text{ °C}$	" each channel:	I _{L(ISO)}	1.8	2.3		А
	both channels parallel:		3.5	4.4		
Output current (pin 1 or 7)	while GND disconnected	I _{L(GNDhigh)}			10	mA
or GND pulled up, V_{bb} =30	V , V_{IN} = 0, see diagram					
page 7						
Turn-on time	IN \int to 90% V_{OUT} :	<i>t</i> on	80	200	400	μs
Turn-off time	IN \perp to 10% V_{OUT} :	$t_{ m off}$	80	200	400	
$R_{\rm L} = 12 \ \Omega, \ T_{\rm j} = -40 + 150^{\circ}$	C					
Slew rate on		dV/dt_{on}	0.1		1	V/μs
10 to 30% V_{OUT} , $R_L = 12 \Omega$	2, <i>T</i> _j =-40+150°C					
Slew rate off 70 to 40% V_{OUT} , $R_L = 12.9$	2, <i>T</i> _i =-40+150°C	-dV/dt _{off}	0.1		1	V/µs
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Operating Parameters

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Operating voltage ⁵⁾	<i>T</i> _j =-40+150°C:	$V_{\rm bb(on)}$	5.0		24	V
Undervoltage shutdown	<i>T</i> _j =-40+150°C:	$V_{ m bb(under)}$	3.5		5.0	V
Undervoltage restart	<i>T</i> _j =-40+150°C:	V _{bb(u rst)}			5.0	V
Undervoltage restart of charge page 10	oump	$V_{ m bb(ucp)}$		5.6	7.0	V
Undervoltage hysteresis $\Delta V_{\text{bb(under)}} = V_{\text{bb(urst)}} - V_{\text{bb(under)}}$		$\Delta V_{ m bb(under)}$		0.2		V
		1.4				
Overvoltage shutdown	$T_{\rm j}$ =-40+150°C:	$V_{ m bb(over)}$	24		34	V
Overvoltage restart	<i>T</i> _j =-40+150°C:	V _{bb(o rst)}	23			V
Overvoltage hysteresis	<i>T</i> _j =-40+150°C:	$\Delta V_{ m bb(over)}$		0.5		V
Overvoltage protection ⁶⁾	<i>T</i> _j =-40+150°C:	$V_{\rm bb(AZ)}$	42	47		V
<i>l</i> _{bb} =40 mA						
Standby current (pin 4)	<i>T</i> _j =-40+25°C:	I _{bb(off)}		14	30	μΑ
V_{IN} =0	<i>T</i> _j = 150°C:			17	35	
Leakage output current (include	d in I _{bb(off)})	I _{L(off)}			12	μΑ
Vin=0						
Operating current (Pin 2) ⁷⁾ , V_{IN} = both channels on, T_{i} =-40+15		I _{GND}		4	6	mA

⁵⁾ At supply voltage increase up to V_{bb} = 5.6 V typ without charge pump, $V_{OUT} \approx V_{bb}$ - 2 V

⁶⁾ See also $V_{
m ON(CL)}$ in table of protection functions and circuit diagram page 7.



Parameter and Conditions, each channel	Symbol		Values		Unit
at $T_j = 25$ °C, $V_{bb} = 12$ V unless otherwise specified		min	typ	max	
Operating current (Pin 2) ⁷⁾ one channel on, $T_i = -40+150$ °C:	I _{GND}		2	3	mA
Protection Functions					
Initial peak short circuit current limit	I _{L(SCp)}				
(pin 4 to 1 or 7) $T_i = -40$ °C: $T_i = 25$ °C: $T_j = +150$ °C:		8 6 3.5	11.5 9 6	15 12 7.5	А
Repetitive short circuit shutdown current limit	I _{L(SCr)}				
$T_{\rm j} = T_{\rm jt}$ (see timing diagrams, page 9)			5		Α
Thermal overload trip temperature	$T_{\rm jt}$	150			°C
Thermal hysteresis	ΔT_{jt}		10		K
Reverse battery (pin 4 to 2) 8)	-V _{bb}			32	V
Reverse battery voltage drop (Vout > Vbb)					
I_{L} = -1.8 A, each channel T_{j} =150 °C:	-V _{ON(rev)}		610		mV
Diagnostic Characteristics					
Open load detection current T_{j} =-40 °C: (on-condition,) T_{j} =25150°C:	I _{L (OL)}	10 10		200 150	mA
Open load detection voltage ⁹⁾ (off-condition) T_j =-40150°C:	$V_{OUT(OL)}$	2	3	4	V
Internal output pull down (pin 1 or 7 to 2), $V_{\text{OUT}}=5 \text{ V}$, $T_{\text{j}}=-40150^{\circ}\text{C}$	Ro	4	10	30	kΩ

⁷⁾ Add I_{ST} , if $I_{ST} > 0$, add I_{IN} , if $V_{IN} > 5.5 \text{ V}$

Requires 150Ω resistor in GND connection. The reverse load current through the intrinsic drain-source diode has to be limited by the connected load. Note that the power dissipation is higher compared to normal operating conditions due to the voltage drop across the intrinsic drain-source diode. The temperature protection is not active during reverse current operation! Input and Status currents have to be limited (see max. ratings page 2 and circuit page 7).

⁹⁾ External pull up resistor required for open load detection in off state.



Parameter and Conditions, each channel	Symbol		Values		Unit
at $T_j = 25$ °C, $V_{bb} = 12$ V unless otherwise specified		min	typ	max	
Input and Status Feedback ¹⁰⁾					
Input resistance $T_{j=-40150^{\circ}\text{C}}$, see circuit page 6	R _I	2.5	3.5	6	kΩ
Input turn-on threshold voltage $\sqrt{T_j}$ =-40+150°C:	$V_{IN(T+)}$	1.7		3.5	V
Input turn-off threshold voltage T_j =-40+150°C:		1.5			V
Input threshold hysteresis	$\Delta V_{\text{IN(T)}}$		0.5		V
Off state input current (pin 3 or 6), $V_{IN} = 0.4 \text{ V}$, $T_j = -40+150$ °C	I _{IN(off)}	1		50	μΑ
On state input current (pin 3 or 6), $V_{IN} = 3.5 \text{ V}$, $T_j = -40+150$ °C	I _{IN(on)}	20	50	90	μΑ
Delay time for status with open load after switch off (other channel in off state) (see timing diagrams, page 10), $T_j = -40+150$ °C	$t_{d(ST\;OL4)}$	100	320	800	μs
Delay time for status with open load after switch off (other channel in on state) (see timing diagrams, page 10), $T_j = -40+150$ °C	t _{d(ST OL5)}		5	20	μs
Status invalid after positive input slope	$t_{d(ST)}$		200	600	μs
(open load)					
Status output (open drain)					
Zener limit voltage $T_j = -40 + 150$ °C, $I_{ST} = +1.6$ mA:	$V_{\rm ST(high)}$	5.4	6.1		V
ST low voltage $T_j = -40 + 25$ °C, $I_{ST} = +1.6$ mA:	$V_{\rm ST(low)}$			0.4	
$T_{\rm j}$ = +150°C, $I_{\rm ST}$ = +1.6 mA:				0.6	

 $^{^{\}rm 10)}\,$ If a ground resistor $R_{\rm GND}$ is used, add the voltage drop across this resistor.



Truth Table

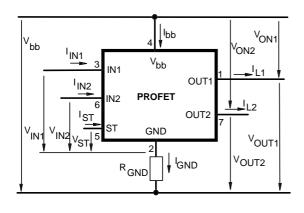
		IN1	IN2	OUT1	OUT2	ST	ST
						BTS610L1	BTS612N1
						BTS611L1	
Normal operation		L	L	L	L	Н	Н
		L	Н	L	Н	Н	Н
		Н	L	Н	L	Н	Н
		Н	Н	Н	Н	Н	Н
Open load	Channel 1	L	L	Z	L	H(L ¹¹⁾)	L
		L	Н	Z	Н	Н	Н
		Н	Х	Н	Х	L L	Н
	Channel 2	L	L	L	Z	H(L ¹¹⁾)	L
		Н	L	Н	Z	Н	Н
		X	Н	Х	Н	L	Н
Short circuit to V _{bb}	Channel 1	L	L	Н	L	L ¹²)	L
		L	Н	Н	Н	H ₁₀	Н
		Н	X	Н	Х	H(L ¹³))	Н
	Channel 2	L	L	L	Н	L ¹²)	L
		Н	L	Н	Н	Η	Н
		X	Н	Х	Н	H(L ¹³⁾)	Н
Overtemperature	both channel	L	L	L	L	Н	Н
		X	Н	L	L	L	L
		Н	Х	L	L	L	L
	Channel 1	L	Х	L	Х	Н	Н
		Н	Х	L	Х	L	L
	Channel 2	Х	L	Х	L	Н	Н
		Х	Н	Х	L	L	L
Undervoltage/ Overvoltage		Х	Х	L	L	Н	Н

L = "Low" Level H = "High" Level X = don't care

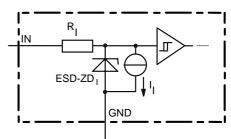
Z = high impedance, potential depends on external circuit

Status signal after the time delay shown in the diagrams (see fig 5. page 10)

Terms



Input circuit (ESD protection)



ESD zener diodes are not to be used as voltage clamp at DC conditions. Operation in this mode may result in a drift of the zener voltage (increase of up to 1 V).

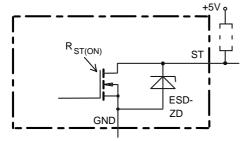
¹¹⁾ With additional external pull up resistor

An external short of output to $V_{\rm bb}$, in the off state, causes an internal current from output to ground. If R_{GND} is used, an offset voltage at the GND and ST pins will occur and the V_{ST low} signal may be errorious.

¹³⁾ Low resistance to $V_{
m bb}$ may be detected in the ON-state by the no-load-detection



Status output

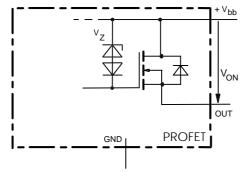


ESD-Zener diode: 6.1 V typ., max 5 mA;

 $R_{ST(ON)}$ < 380 Ω at 1.6 mA, ESD zener diodes are not to be used as voltage clamp at DC conditions.

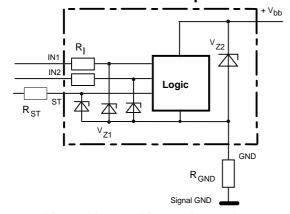
Operation in this mode may result in a drift of the zener voltage (increase of up to 1 V).

overvoltage output clamp



Von clamped to 47 V typ.

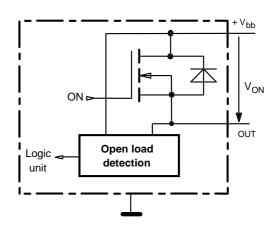
Overvolt. and reverse batt. protection



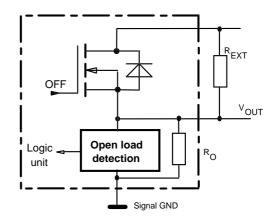
 $V_{\rm Z1}$ = 6.1 V typ., $V_{\rm Z2}$ = 47 V typ., $R_{\rm I}$ = 3.5 k Ω typ, $R_{\rm GND}$ = 150 Ω

Open-load detection

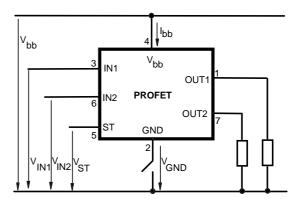
ON-state diagnostic condition: $V_{ON} < R_{ON} * I_{L(OL)}$; IN high



OFF-state diagnostic condition: $V_{OUT} > 3 \text{ V typ.}$; IN low



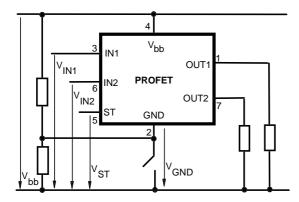
GND disconnect



In case of Input=high is $V_{\rm OUT} \approx V_{\rm IN}$ - $V_{\rm IN(T+)}$. Due to $V_{\rm GND}$ >0, no $V_{\rm ST}$ = low signal available.

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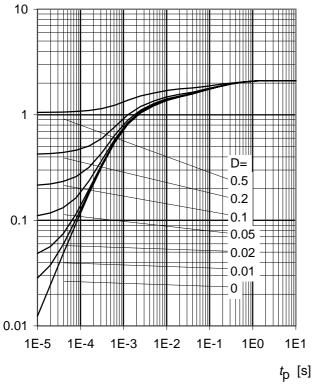
GND disconnect with GND pull up

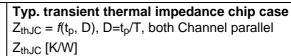


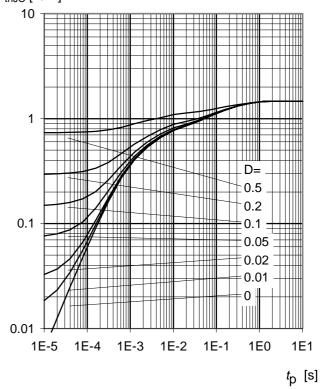
If $V_{GND} > V_{IN} - V_{IN(T+)}$ device stays off Due to $V_{GND} > 0$, no $V_{ST} =$ low signal available.

Typ. transient thermal impedance chip case

 $Z_{thJC} = f(t_p, D), D=t_p/T$, one Channel active Z_{thJC} [K/W]







Timing diagrams

Both channels are symmetric and consequently the diagrams are valid for each channel as well as for permuted channels

Figure 1a: V_{bb} turn on:

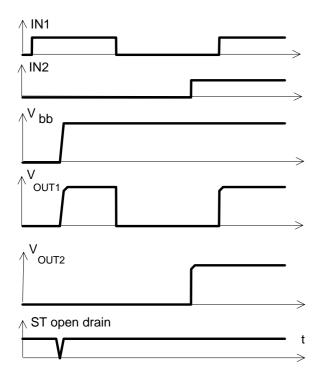


Figure 2a: Switching a lamp:

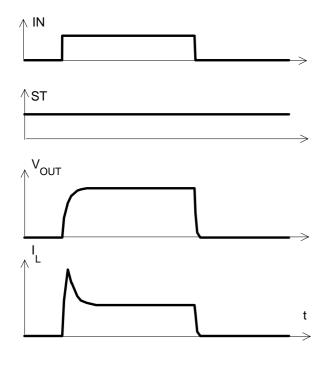
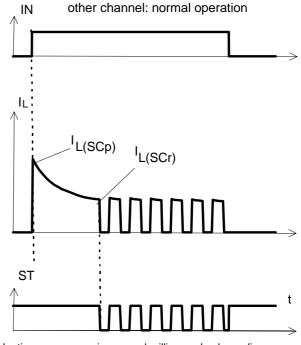
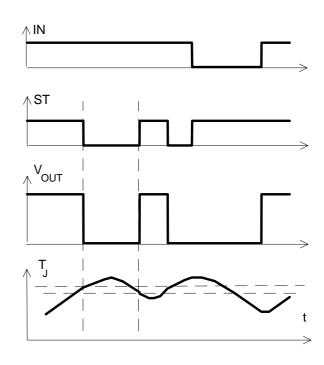


Figure 3a: Short circuit shut down by overtempertature, reset by cooling



Heating up may require several milliseconds, depending on external conditions

Figure 4a: Overtemperature: Reset if $T_i < T_{it}$



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Figure 5a: Open load: detection in ON-state, open load occurs in on-state

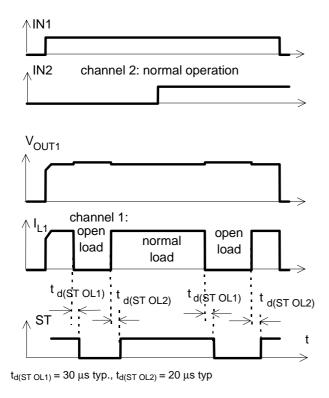


Figure 5b: Open load: detection in ON-state, turn on/off to open load

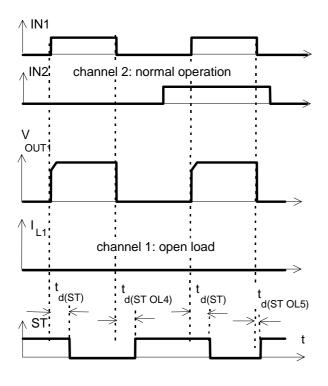
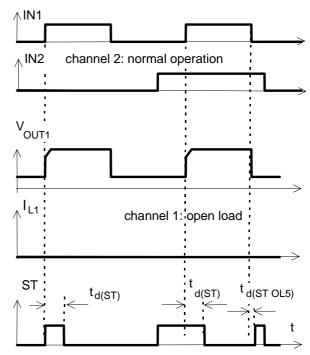


Figure 5c: Open load: detection in ON- and OFF-state (with R_{EXT}), turn on/off to open load



 $t_{d(ST\ OL5)}$ depends on external circuitry because of high impedance

Figure 6a: Undervoltage:

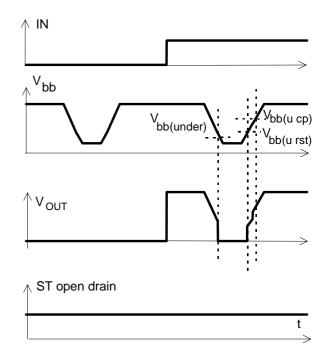
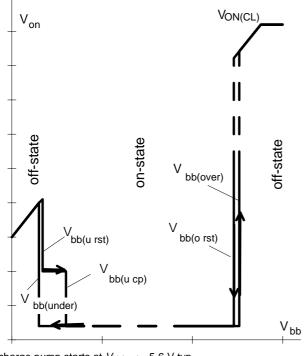


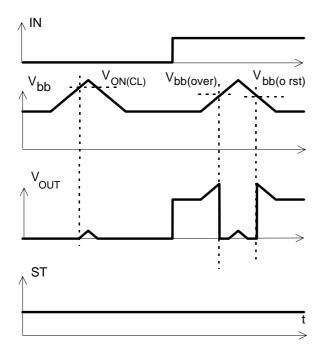


Figure 6b: Undervoltage restart of charge pump



charge pump starts at $V_{\rm bb(ucp)}$ =5.6 V typ.

Figure 7a: Overvoltage:





Package and Ordering Code

All dimensions in mm

 Standard TO-220AB/7
 Ordering code

 BTS610L1
 Q67060-S6300-A2

